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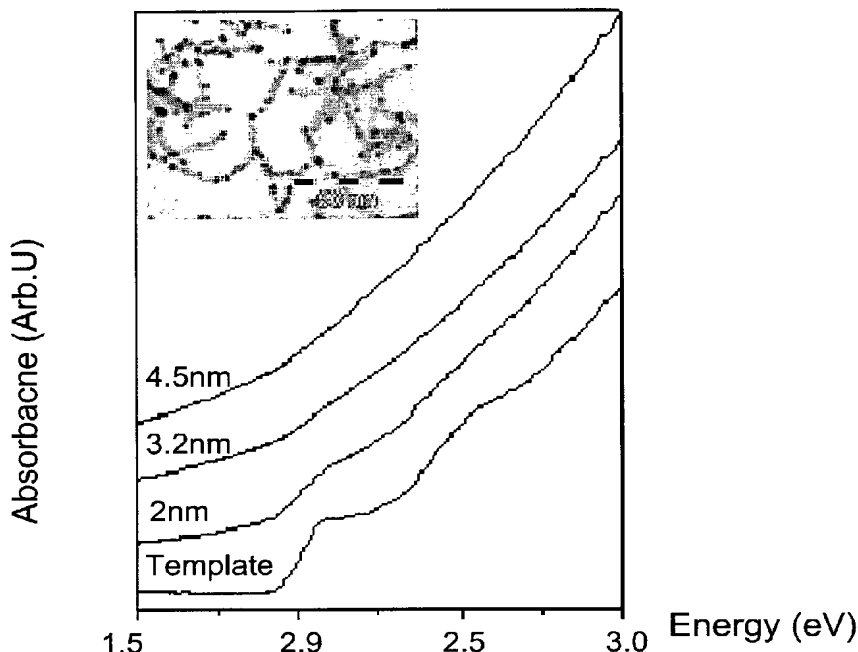
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(54) Title: NOVEL NANOSTRUCTURES AND METHOD FOR SELECTIVE PREPARATION



(57) Abstract: The present invention provides novel nanostructure composed of at least one elongated structure element, an elongated structure element of said nanostructure bearing a different zone made of metal, metal alloy, conductive polymer or semiconductor and selectively grown onto at least one of the end portions of the elongated structure element. The present invention further provides a selective method for forming in a liquid medium, such nanostructures.



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